In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (Original) A thin film transistor-LCD, comprising:
a transparent substrate provided with at least two adjacent gate electrodes;
a gate insulating layer on the gate electrodes;
a semiconductor layer in a predetermined shape on the insulating layer;
a source/drain electrode layer on a predetermined area of the transparent substrate;
an insulating layer on the source/drain electrode layer;
a contact hole via the insulating layer, source/drain electrode layer, and gate insulating layer, exposing a part of the surface of transparent substrate between the adjacent gate electrodes;
a transparent conductive layer on the transparent substrate; and
a light-shielding matrix directly above the contact hole.

2. (Original) The thin film transistor-LCD as claimed in claim 1, wherein the gate electrode is a Mo-Al-Nd electrode.

3. (Original) The thin film transistor-LCD as claimed in claim 1, wherein the source/drain electrode layer is an Al, Al-Nb, Al-Nd, Al-Ti or Al-Si-Cu layer.

4. (Original) The thin film transistor-LCD as claimed in claim 1, wherein the gate insulating layer is an oxide layer formed by chemical vapor deposition.

5. (Original) The thin film transistor-LCD as claimed in claim 1, wherein the insulating layer is an oxide or nitride layer formed by chemical vapor deposition.

6. (Original) The thin film transistor-LCD as claimed in claim 1, further comprising a color filter a predetermined distance above the transparent substrate, wherein the light-shielding matrix directly above the contact hole is disposed on the color filter.

7. (Original) The thin film transistor-LCD as claimed in claim 1, wherein the gate electrodes are separate from the contact hole.

8. (Original) A thin film transistor-LCD, comprising:

a transparent substrate provided with at least two adjacent gate electrodes;

a gate insulating layer on the gate electrodes;

a semiconductor layer in a predetermined shape on the insulating layer;

a source/drain electrode layer on a predetermined area of the transparent substrate;

an insulating layer on the source/drain electrode layer;

a contact hole, separate from the gate electrodes, via the insulating layer, source/drain electrode layer, and gate insulating layer, exposing a part of the surface of transparent substrate between the adjacent gate electrodes;

an indium thin oxide layer on the transparent substrate;

a color filter provided a predetermined distance above the transparent substrate; and

a light-shielding matrix on the color filter, directly above the contact hole.

9. (Original) The thin film transistor-LCD as claimed in claim 8, wherein the gate electrode is a Mo-Al-Nd electrode, and the source/drain electrode layer is an Al, Al-Nb, Al-Nd, Al-Ti or Al-Si-Cu layer.

10. (Original) The thin film transistor-LCD as claimed in claim 8, wherein the gate insulating layer is an oxide layer and the insulating layer is an oxide or nitride layer formed by chemical vapor deposition.

11. – 20. Canceled.